

# PROCEEDINGS OF SPIE

## Oxide-based Materials and Devices XI

**David J. Rogers**

**David C. Look**

**Ferechteh H. Teherani**

*Editors*

**3–6 February 2020**

**San Francisco, California, United States**

*Sponsored and Published by*

**SPIE**

**Volume 11281**

Proceedings of SPIE 0277-786X, V. 11281

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

Oxide-based Materials and Devices XI, edited by David J. Rogers, David C. Look,  
Ferechteh H. Teherani, Proc. of SPIE Vol. 11281, 1128101 · © 2020 SPIE  
CCC code: 0277-786X/20/\$21 · doi: 10.1117/12.2567567

Proc. of SPIE Vol. 11281 1128101-1

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Author(s), "Title of Paper," in *Oxide-based Materials and Devices XI*, edited by David J. Rogers, David C. Look, Ferecheh H. Teherani, Proceedings of SPIE Vol. 11281 (SPIE, Bellingham, WA, 2020) Seven-digit Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510633254

ISBN: 9781510633261 (electronic)

Published by

**SPIE**

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) · Fax +1 360 647 1445

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